

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Masanobu Senda, et al.

Serial No.: Not Yet Assigned Group Art Unit: Not Yet Assigned

Filing Date: Concurrently Herewith Examiner: Unknown

For: SEMICONDUCTOR LIGHT EMITTING ELEMENT AND METHOD OF
MAKING SAME

Honorable Commissioner of Patents
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

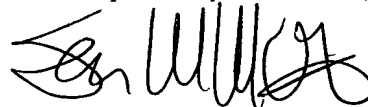
Under the provisions of 37 CFR §1.97 through §1.99 and pursuant to applicant's duty of disclosure under 37 CFR §1.56, applicant respectfully brings the following documents listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. Copies of the listed documents are provided herewith for the convenience of the Examiner. In compliance with the concise explanation requirement under 37 CFR §1.98(a)(3), the relevance of these documents are discussed on pages 1, 2, 3, and 4 of the subject application. Further, English-language Abstracts are attached to some of the references.

This citation does not constitute an admission that the references are relevant or material to the claims. They are only cited as constituting related art of which the applicant is aware.

It is respectfully requested that the listed references be considered by the Examiner and formally made of record in this application.

Please charge any deficiencies in fees and credit any overpayment of fees to Attorney's Deposit Account No. 50-0481.

Respectfully submitted,



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INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

ATTY DOCKET NO.

PTGF-03093

SERIAL NO.

Not Yet Assigned

Masanobu Senda, et al.

FILING

Concurrently Herewith

GROUP

Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	2000-021789	01/21/2000	Japan			ABS (only)	
	2000-357663	12/26/2000	Japan			ABS	
	11-130597	05/18/1999	Japan			ABS	
	2001-160657	06/12/2001	Japan			ABS	
	2002-164296	06/07/2002	Japan			ABS	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Yoshiaki Honda, et al., "Transmission Electron Microscopy Investigation of Dislocations in GaN Layer Grown by Facet-Controlled Epitaxial Lateral Overgrowth", Japanese Journal of Applied Physics, Vol. 40, April 1, 2001, pp. L309-L312.
		Hiromitsu Mizutani, et al., "Reduction of dislocation density in GaN using FACELO (Facet Controlled Epitaxial Lateral Overgrowth)", Technical Report of IEICE, ED2000-22, CPM2000-7, SDM2000-22 (2000-05), pp. 35-40.

EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

